





FORMING A TEST PATTERN IN SELECTED FIELDS OF A FIRST LAYER ON A SEMICONDUCTOR SUBSTRATE

FORMING A LAYER OF PHOTORESIST OVER THE FIRST LAYER

FORMING LATENT IMAGES IN PORTIONS OF THE PHOTORESIST LAYER LYING IN THE SELECTED FIELDS OVER THE TEST PATTERN OF THE FIRST LAYER

MEASURING THE ALIGNMENT OF THE TEST PATTERN IN THE SELECTED FIELDS OF THE FIRST LAYER WITH THE OVERLYING LATENT IMAGES IN THE PHOTORESIST LAYER USING SCATTEROMETRY

EXPOSE REMAINING FIELDS ON SEMICONDUCTOR SUBSTRATE USING ALIGNMENT CORRECTIONS BASED ON TEST FIELD OVERLAY MEASUREMENTS